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# 2SJ527(L), 2SJ527(S)

Silicon P Channel MOS FET  
High Speed Power Switching

## HITACHI

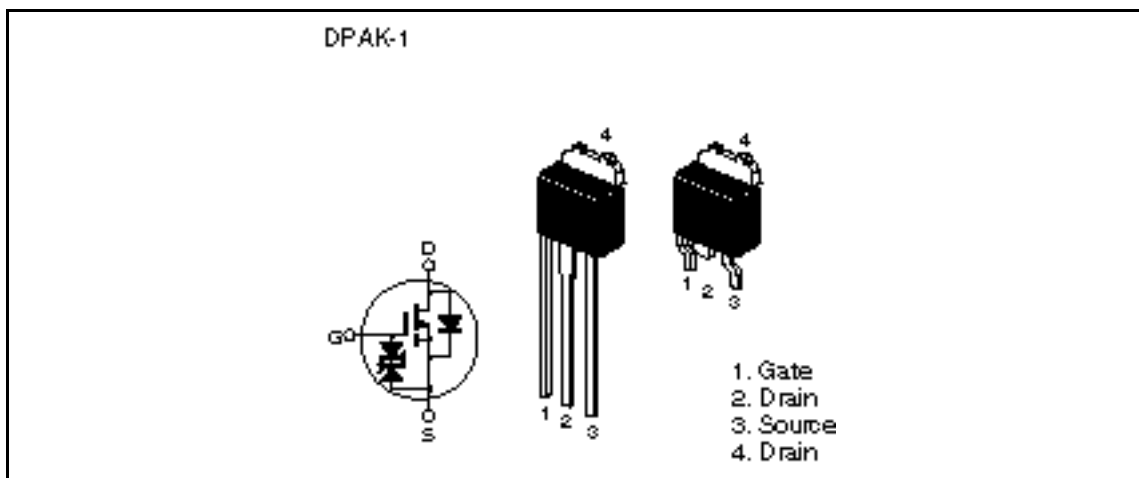
ADE-208-640A (Z)  
2nd. Edition  
Jun 1998

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### Features

- Low on-resistance  
 $R_{DS(on)} = 0.3 \quad \text{typ.}$
- Low drive current
- 4 V gate drive devices
- High speed switching

### Outline



## 2SJ527(L),2SJ527(S)

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	-5	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	-20	A
Body-drain diode reverse drain current	$I_{DR}$	-5	A
Avalanche current	$I_{AP}$ <sup>Note3</sup>	-5	A
Avalanche energy	$E_{AR}$ <sup>Note3</sup>	2.1	mJ
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	20	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

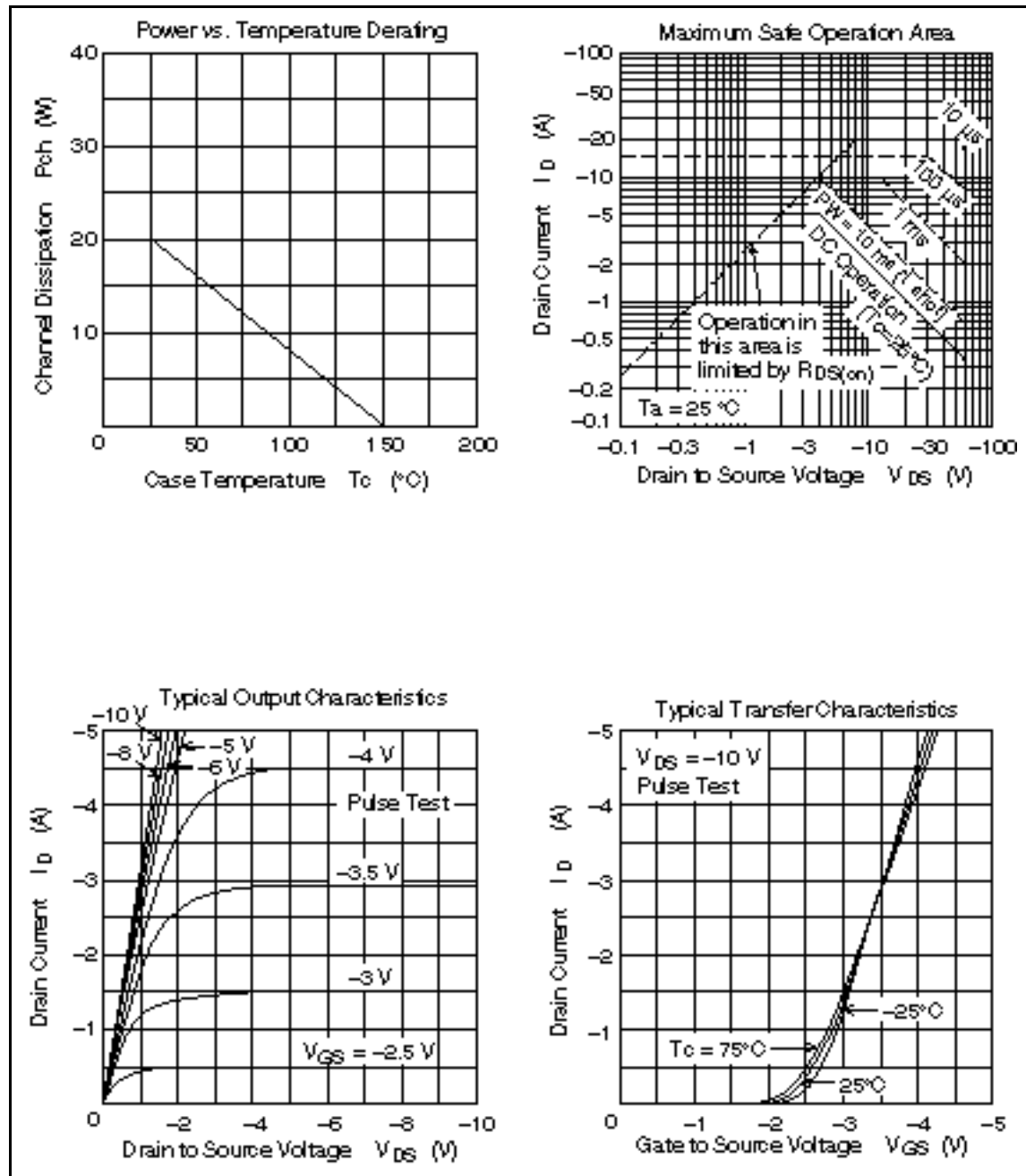
Note: 1. PW 10μs, duty cycle 1 %  
 2. Value at Tc = 25°C  
 3. Value at Tch = 25°C, Rg 50

### Electrical Characteristics (Ta = 25°C)

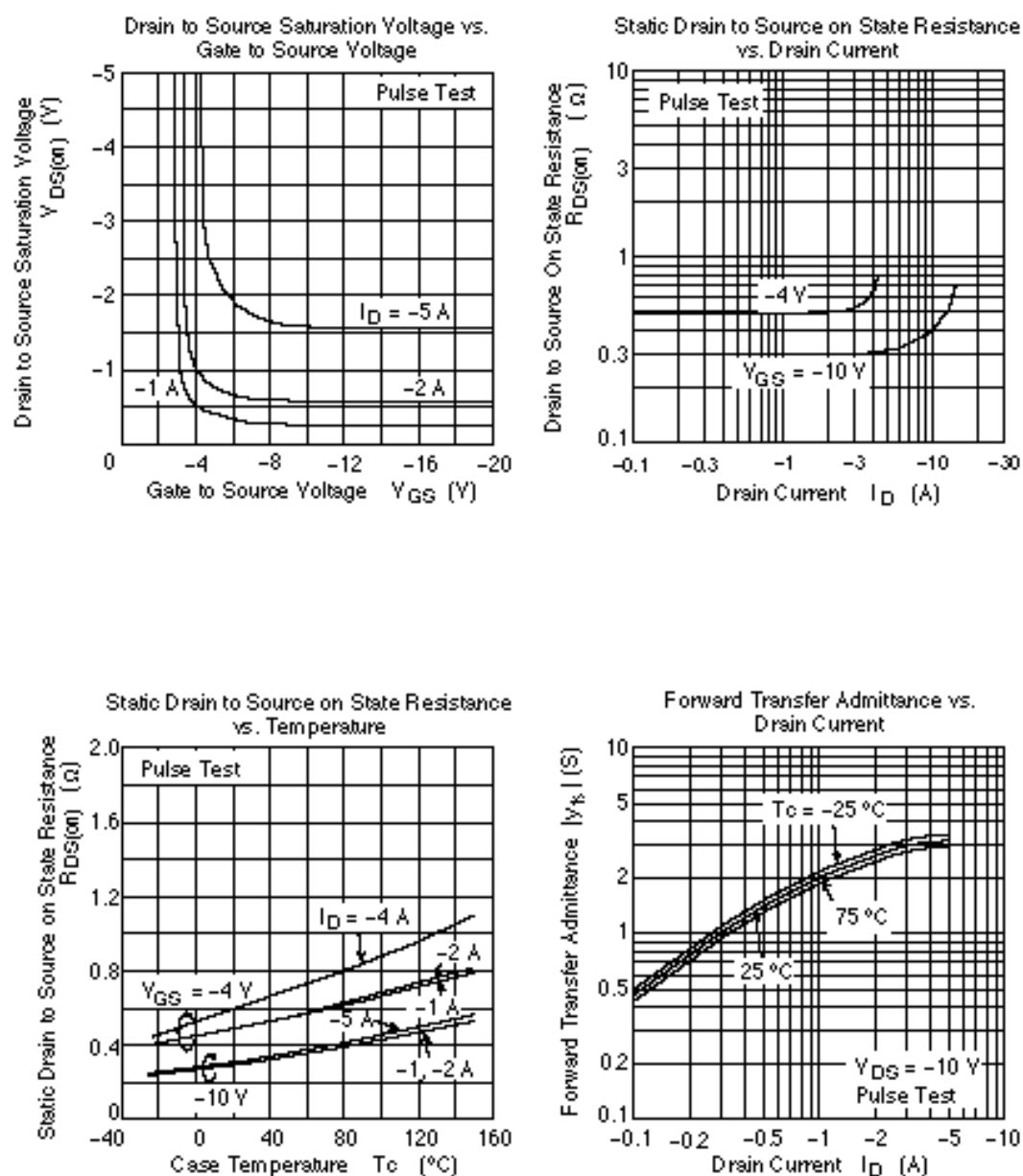
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-10	μA	$V_{DS} = -60V, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1mA, V_{DS} = -10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.3	0.4		$I_D = -3A, V_{GS} = -10V$ <sup>Note4</sup>
	$R_{DS(on)}$	—	0.5	0.8		$I_D = -3A, V_{GS} = -4V$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	1.8	3	—	S	$I_D = -3A, V_{DS} = -10V$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	220	—	pF	$V_{DS} = -10V$
Output capacitance	$C_{oss}$	—	110	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	35	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{GS} = -10V, I_D = -3A$
Rise time	$t_r$	—	30	—	ns	$R_L = 10$
Turn-off delay time	$t_{d(off)}$	—	45	—	ns	
Fall time	$t_f$	—	35	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	-1.35	—	V	$I_F = -5A, V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	55	—	ns	$I_F = -5A, V_{GS} = 0$ $diF/dt = 50A/\mu s$

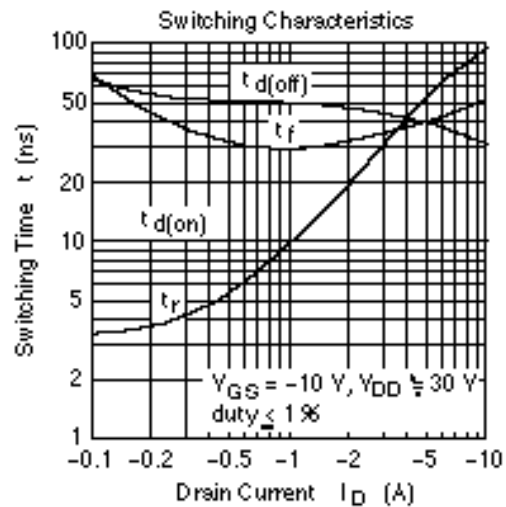
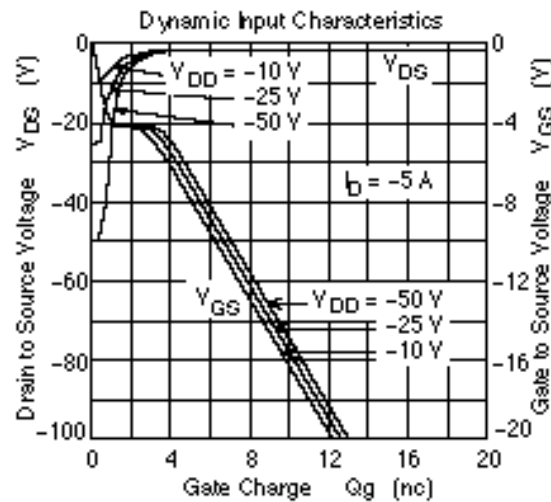
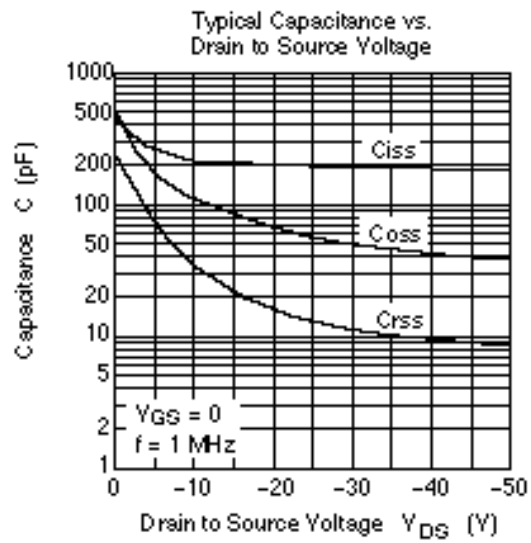
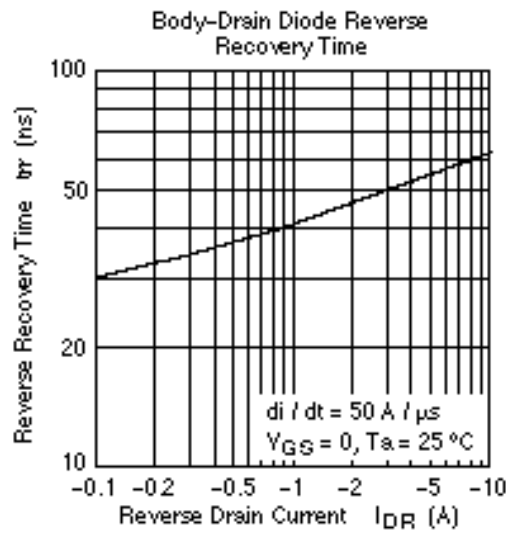
Note: 4. Pulse test

# Main Characteristics

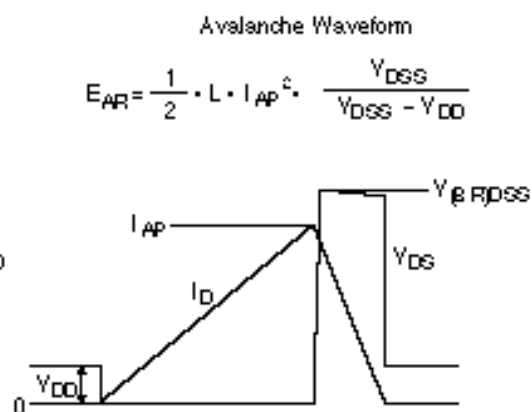
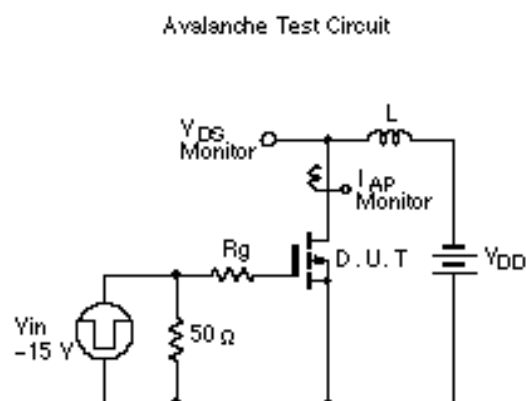
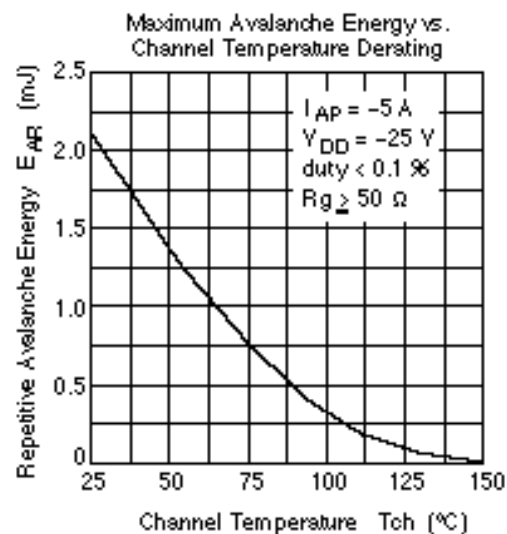
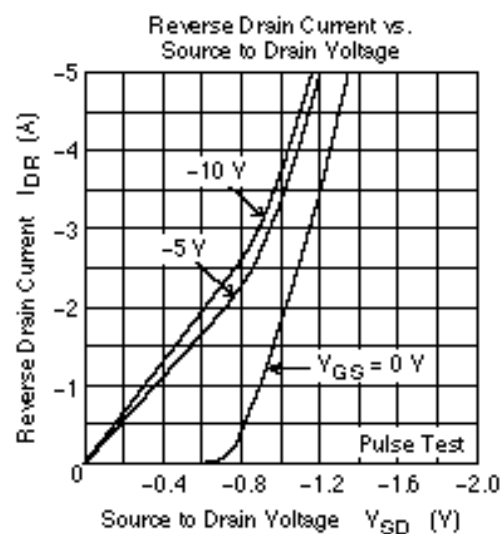


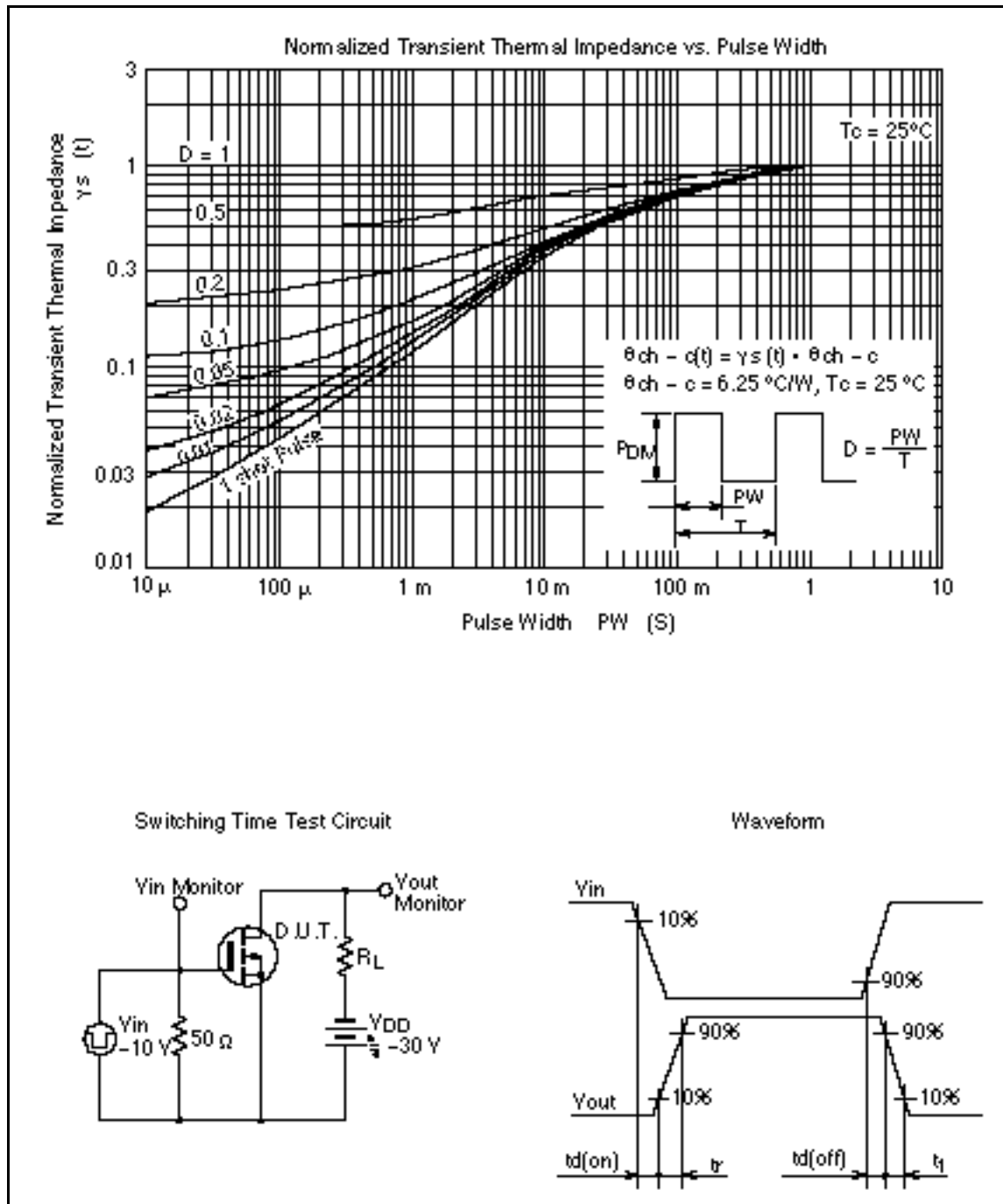
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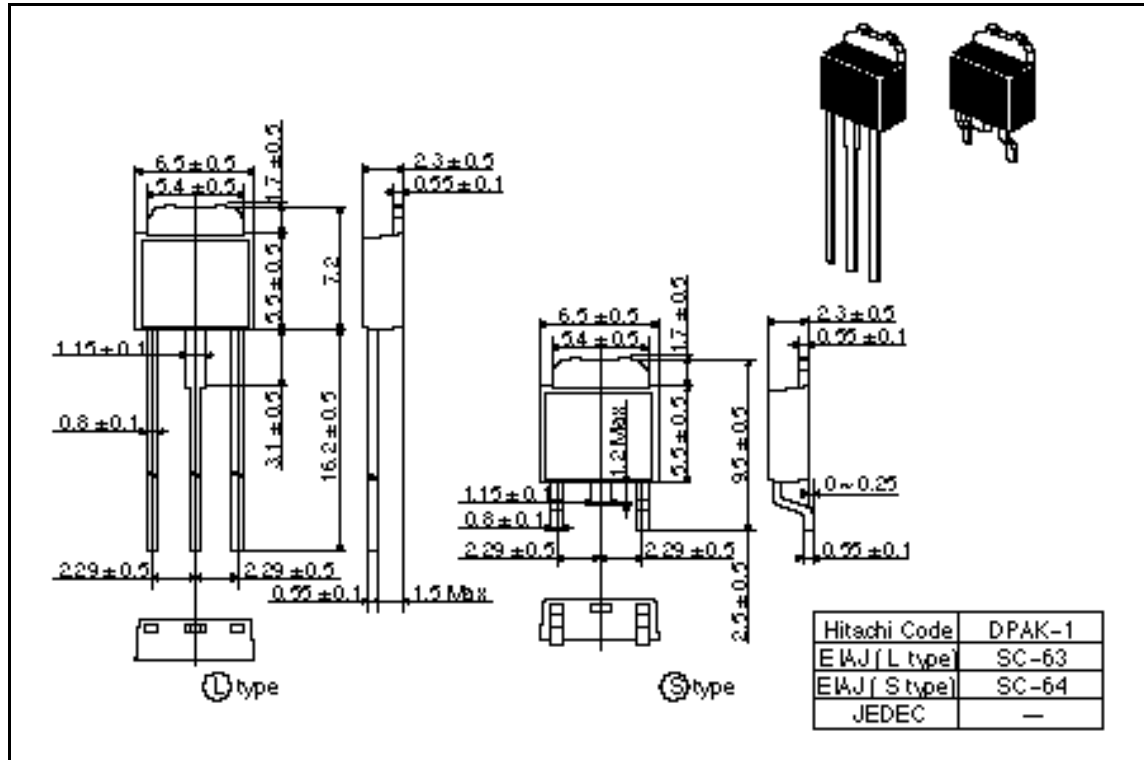




## 2SJ527(L),2SJ527(S)

### Package Dimensions

Unit: mm





## Cautions

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